ABSTRACT

In a method for forming a dual damascene structure in a semiconductor device, an insulating layer is formed on a semiconductor substrate and a silicon nitride etch stop layer is formed on the insulating layer. Then a photoresist layer is applied on the etch stop layer for a contact hole pattern. Thereafter, the insulating layer is etched according to the contact hole pattern and the rest etch stop layer is pull back etched to expose upper surface of the insulating layer. The insulating layer is etched again according to the modified pattern of the rest etch stop layer and the rest etch stop layer is removed so that a dual damascene structure is completed. Therefore, a dual damascene structure can be made by using a single photoresist process and a single etch stop layer so that a manufacturing process is simplified.